

## Product Change Notice

(PCN No.: 04/08)

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Customer: All

IXYS product type: All 1200V IGBT products, which contains 1200V NPT<sup>3</sup> IGBTs

MWI ...-12E6K	MKI ...-12E7	MIL...-12E4	MUBW...-12E6K	IXE...N120	FIL...-12E
MWI ...-12E7	MKI...-12E8	MID...-12E4	MUBW...-12E7	IXE...N120D1	FIO50-12BD
MWI...-12E8		MDI...-12E4	MUBW....-12E8		
MWI...-12E9					

Description of change: Phosphorous implantation for the aSi layer, which connects the metal field plates of the junction termination, is skipped.

Reason for change: The new design of field plates allows to reduce the conductivity of the aSi. This change reduces collector leakage current.

Identification: N/A

Schedule of change: The change is effective as of now.

Influence on reliability: The change has no repercussions on any other electrical device characteristics than mentioned above.

Internal reference: *ÄA 031/08,*

In case of any question, please contact

Initiator	Title/Function	Date	e-mail
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**Customer response:**  
**(please fill in and return by e-mail, fax or mail within 4 weeks)**

for further questions / information      Company: \_\_\_\_\_

please comment      Name & Position: \_\_\_\_\_

Phone / Fax No.: \_\_\_\_\_

Note: **Written** response or **written** acknowledgement with statement of approval criteria, must be received within thirty (30) days of the date of this PCN or IXYS will consider this change approved.

Comments:

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